

High-reliability discrete products and engineering services since 1977

2N6050-2N6052(PNP) 2N6057-2N6059(NPN)

COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Rating	Symbol	2N6057 2N6050	2N6058 2N6051	2N6059 2N6052	Units
Collector-base voltage (I _E = 0)	V _{CBO}	60	80	100	V
Collector-emitter voltage (V _{BE} = -1.5V)	V _{CEX}	60	80	100	V
Collector-emitter voltage (I _B = 0)	V _{CEO}	60	80	100	V
Emitter base voltage (I _C = 0)	V _{EBO}	5.0		٧	
Collector current – continuous	Ic	12		Α	
Collector current – peak	I _{CM}	20		А	
Base current	I _B	0.2		А	
Total power dissipation T _c ≤ 25°C	P _D	150		W	
Operating and storage junction temperature range	T _J , T _{stg}	-65 to +200		Č	
Thermal resistance, junction to case	R _{thj-c}	1.170		°C/W	

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise specified)

Characteristics (1 c = 25 Cuttless otherwise specified)						
Characteristic		Symbol	Min	Max	Unit	
OFF CHARACTERISTICS		·				
Collector cutoff current						
(V_{CE} = rated V_{CEX} , $V_{BE(off)}$ = -1.5V)		I _{CEX}	-	0.5	mA	
(V_{CE} = rated V_{CEX} , $V_{BE(off)}$ = -1.5V, T_C = 150°C)			-	5.0		
Collector cutoff current						
$(V_{CE} = 30V, I_B = 0)$	2N6050, 2N6057		-	1.0	mA	
$(V_{CE} = 40V, I_B = 0)$	2N6051, 2N6058	I _{CEO}	-	1.0		
$(V_{CE} = 50V, I_B = 0)$	2N6052, 2N6059		-	1.0		
Emitter cutoff current				2.0	^	
$(I_C = 0, V_{EB} = 5.0V)$		I _{EBO}	-	2.0	mA	
Collector-emitter sustaining voltage (1)	2N6050, 2N6057		60	-		
$(I_C = 100mA)$	2N6051, 2N6058	$V_{CEO(sus)}$	80	-	V	
	2N6052, 2N6059		100	-		
Collector emitter saturation voltage (1)						
$(I_C = 6A, I_B = 24mA)$		$V_{CE(sat)}$	-	2.0	V	
$(I_C = 12A, I_B = 120mA)$			-	3.0		
Base emitter saturation voltage (1)			-	4.0	V	
$(I_C = 12A, I_B = 120mA)$		$V_{BE(sat)}$				
Base emitter on voltage (1)		.,		2.0	.,	
$(I_C = 6A, V_{CE} = 3.0V)$		V _{BE(ON)}	-	2.8	V	



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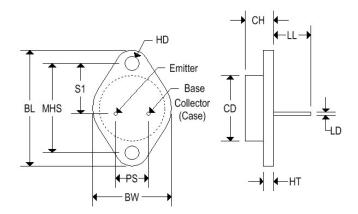
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise specified)

Characteristic	Symbol	Min	Мах	Unit
DC current gain (1)				
$(I_C = 6A, V_{CE} = 3.0V)$	h _{FE}	750	-	-
$(I_C = 12A, V_{CE} = 3.0V)$		100	-	
Transition frequency (I _C = 5.0A, V _{CE} = 3.0V, f = 1.0MHz)	f⊤	4	-	MHz

Note 1: Pulse test: pulse width ≤ 300µs, duty cycle ≤ 1.5%.

MECHANICAL CHARACTERISTICS

Case	TO-3
Marking	Alpha-numeric
Pin out	See below



	TO-3				
	Inc	hes	Millimeters		
	Min	Max	Min	Max	
CD	-	0.875	-	22.220	
CH	0.250	0.380	6.860	9.650	
HT	0.060	0.135	1.520	3.430	
BW	ı	1.050	-	26.670	
HD	0.131	0.188	3.330	4.780	
LD	0.038	0.043	0.970	1.090	
LL	0.312	0.500	7.920	12.700	
BL	1.550	REF	39.37	39.370 REF	
MHS	1.177	1.197	29.900	30.400	
PS	0.420	0.440	10.670	11.180	
S1	0.655	0.675	16.640	17.150	